## **Supplementary information**

## Optical Quantum Confinement and Photocatalytic Properties in Two-, One-, and Zero-Dimensional Nanostructures

Tomas Edvinsson

Department of Engineering Sciences, Solid State Physics, Ångström Laboratory, Uppsala University, Box 534, 75121 Uppsala, Sweden

### 1. Key data for potential dependent absorption spectroscopy

**Table S1.** Key data for potential dependent absorption spectroscopy for ZnO quantum dots with diameters between 4.4 and 8.6 nm utilized for analysis of Burstein-Moss bleach discussed in main article. The potentials (V) are all reported *versus* the normal hydrogen electrode (NHE). The flatband potential (E<sub>fb</sub>) reported in the table is determined by electrochemical impedance spectroscopy (EIS).

Sample	E <sub>g</sub> [eV]	d [nm]	E <sub>cb</sub> B (V)	Е <sub>сь</sub> Ј (V)	Е <sub>fb</sub> М 1225 Hz (V	Е <sub>fb</sub> М 3160 Hz (V)	dE <sub>g</sub> /dU	U at I <sub>min</sub> (V)
1	3.57	4.39	-0.83	-0.79	-0.60	-0.62	-1.30	-0.76
2	3.53	4.89	-0.79	-0.77	-0.59	-0.61	-1.16	-0.68
3	3.52	4.91	-0.76	-0.72	-0.50	-0.53	-1.30	-0.69
4	3.51	5.10	-0.77	-0.75	-0.53	-0.54	-1.48	-0.72
5	3.50	5.22	-0.76	-0.74	-0.54	-0.55	-1.46	-0.70
6	3.49	5.36	-0.75	-0.72	-0.51	-0.53	-1.15	-0.68
7	3.49	5.42	-0.71	-0.68	-0.50	-0.57	-1.26	-0.67
8	3.45	6.15	-0.75	-0.75	-0.49	-0.50	-0.68	-0.69
9	3.45	6.19	-0.73	-0.73	-0.51	-0.52	-0.76	-0.69
10	3.43	6.65	-0.71	-0.73	-0.49	-0.52	-0.57	-0.69
11	3.43	6.72	-0.70	-0.72	-0.52	-0.53	-0.72	-0.70
12	3.42	7.08	-0.69	-0.70	-0.46	-0.48	-0.74	-0.65
13	3.42	7.12	-0.68	-0.69	-0.45	-0.47	-0.85	-0.66
14	3.42	7.15	-0.68	-0.72	-0.49	-0.50	-0.50	-0.67
15	3.42	7.19	-0.68	-0.72	-0.45	-0.46	-0.60	-0.66
16	3.41	7.30	-0.66	-0.65	-0.44	-0.46	-0.52	-0.60
17	3.40	8.01	-0.64	-0.65	-0.67	-0.83	-0.84	-0.38
18	3.39	8.56	-0.63	-0.68	-0.86	-1.20	-0.48	-0.41

# 2. Derivation of the joint density of states, equation (8) in the main manuscript

Equation (4) in the main article is

$$T_{\nu \to c} = \frac{2\pi}{\hbar} \int_{BZ} \frac{1}{4\pi^3} |H'_{\nu c}|^2 \delta (E_c(\mathbf{k}) - E_\nu(\mathbf{k}) - \hbar \omega) d\mathbf{k}$$
(S1)

Considering a direct transition (no change in the crystal momentum between the initial,  $k_i$ , and final states,  $k_j$ ), the perturbation matrix element between the corresponding states is then effectively independent of the *k*-vector within the BZ, and can be taken outside the integral to obtain

$$T_{\nu \to c} = \frac{2\pi}{\hbar} \left| H_{\nu c}' \right|^2 g_{\nu c} \left( \hbar \omega \right) \tag{S2}$$

where

$$g_{\nu c}(\hbar\omega) = \int_{BZ} \frac{1}{4\pi^3} \delta(E_c - E_\nu - \hbar\omega) d\mathbf{k}$$
(S3)

 $g_{\mu}(\hbar\omega)$  is here the joint density of states. Evaluation of the integral in (S3) can be performed by using the integral properties of the delta function

$$\int_{a}^{b} g(x)\delta(f(x))dx = \sum_{x_0} g(x_0) \left| \frac{\partial f(x)}{\partial x} \right|_{x=x_0}$$
(S4)

with  $f(x_0)=0$  and  $a < x_0 < b$ . To ensure that  $f(x_0)=0$  in the interval [a,b]. A constant energy different surface between S and S+dS (between the valence and conduction band), valid at each k-point in the Brillouin zone have to be contructed with  $d\mathbf{k}=dSdk_n$  where dkn is a wave vector normal to S. Since  $|\nabla_k E| = dE/dk_n$ , the constant energy difference can be expressed as

$$d\mathbf{k} = dSdk_n = dS \left[ \frac{d(E_c - E_v)}{\left| \nabla_k (E_c - E_v) \right|_{Ec - Ev = \hbar\omega}} \right]$$
(S5)

Utilizing  $d\mathbf{k}$  in (S3),(S4) and integrate over the constant  $d(E_c-E_v)$  one obtain

$$g_{\nu c}(\hbar\omega) = \frac{1}{4\pi^3} \int \frac{dS}{\left|\nabla_k (E_c - E_\nu)\right|_{Ec - E\nu = \hbar\omega}}$$
(S6)

and can be calculated if the functional form of  $E_c$  and  $E_r$  is known. Close to the band edges, the band structure energy can be expanded (with a truncation after the second order term ) as

$$E_{\nu}(k) = E_{\nu}(k_0 + \kappa) = E_{\nu}(k_0) + \frac{1}{2} \sum_{\alpha\beta} \frac{\partial^2 E}{\partial k_{\alpha} \partial k_{\beta}} \kappa_{\alpha} \kappa_{\beta}$$
(S7)

$$E_{c}(k) = E_{c}(k_{0} + \kappa) = E_{c}(k_{0}) + \frac{1}{2} \sum_{\alpha\beta} \frac{\partial^{2} E}{\partial k_{\alpha} \partial k_{\beta}} \kappa_{\alpha} \kappa_{\beta}$$
(S8)

where k is the crystal momentum,  $k_{\theta}$  is the crystal momentum at the band edge at the  $\Gamma$ -point  $E_{\nu}$  is the valence band energy,  $E_c$  is the conduction band energy, and  $\kappa$  is the crystal momentum in reciprocal space for two linear independent directions, a and  $\beta$ .

For isotropic parabolic dispersion close to the band edges, the electrons and holes can be described by a constant direction-independent parameter the effective mass), where the electrons and holes are described as effectively free carriers close band edges *via* 

$$E_{v}(k) = E_{v}(0) - \frac{\hbar^{2}k^{2}}{2m_{p}^{*}}$$
(S9)

$$E_{c}(k) = E_{c}(0) + \frac{\hbar^{2}k^{2}}{2m_{n}^{*}}$$
(S10)

with notations taken from the main article. Utilizing equation (7) in the main article and the energy difference in (S6) we have

$$\left|\nabla_{k}(E_{c}-E_{v})\right| = \frac{\hbar^{2}k}{m_{red}^{*}}$$
(S11)

which together with (S6) gives the joint density of states

$$g_{vc}(\hbar\omega) = \frac{1}{4\pi^3} \left[ 4\pi k^2 \left( \frac{m_{red}^*}{\hbar^2 k} \right) \right]_{Ec-Ev=\hbar\omega} = \frac{1}{2\pi^2} \left( \frac{2m_{red}^*}{\hbar^2} k \right)_{Ec-Ev=\hbar\omega}$$
(S12)

Expressing  $k = (2m_{rd}^*/\hbar^2)^{1/2} (\hbar\omega - E_g)^{1/2}$  we then have

$$g_{vc}(\hbar\omega) = \frac{1}{2\pi^2} \left(\frac{2m_{red}^*}{\hbar^2}\right)^{3/2} (\hbar\omega - E_g)^{1/2}$$
(S13)

Which is equation (8) in the main article.

#### Justification:

A justification of eqn (S13) can be done by reformulating the density of states on the energy scale, g(E), from the definition g(E)dE=2g(k)dk where a factor of 2 is introduced from the two electron spins allowed for each k state. This gives g(E)=2g(k) / (dE/dk) where dE/dk is the E-k dispersion curve valid under isotropic bands. The number of states per unit volume in k-space is  $1/2\pi^3$  for the incremental volume between k and k+dk  $(4\pi k^2 dk)$  and give  $g(k)=k^2/2\pi^2$ .

In the parabolic approximation for the conduction band (given by eqn. (S8)) we have

$$g_{c}(E) = \frac{1}{2\pi^{2}} \left(\frac{2m_{n}^{*}}{\hbar^{2}}\right)^{3/2} \left(E - E_{c}\right)^{1/2}$$
(S14)

The combined density of states,  $g_{ij}$ , can then be introduce *ad hoc* within the parabolic approximation by combining equation (S12) with (S9) and (S10), which leads directly to the joint density of states expressed from the reduced effective mass and the bandgap

$$g_{vc}(h\omega) = \frac{1}{2\pi^2} \left(\frac{2m_{red}^*}{\hbar^2}\right)^{3/2} (\hbar\omega - E_g)^{1/2}$$
(S15)

Although this leads to the same equation as equation (S13), the *ad hoc* replacement of separate effective masses to the reduced mass use the hidden assumption of the existence of a constant energy difference surface between the respective bands as shown above.